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Application Number	10/022,364
Filing Date	12-20-01
First Named Inventor	Kub et al
Group Art Unit	2822
Examiner Name	

(use as many sheets as necessary)

Sheet 1 of 3

Attorney Docket Number NC 79.684

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.1	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code2 (if known)			
SP	A	5374564		Michel Bruel	12-20-1994	
SP	B	5391257		Sullivan et al	2-21-1995	
SP	C	5401544		Nakahata et al	3-28-1995	
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SP	F	5630949		Kenneth M. Lakin	5-20-1997	
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FOREIGN PATENT DOCUMENTS

[illegible]

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/022364
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First Named Inventor	Kub et al
Group Art Unit	9823
Examiner Name	
Attorney Docket Number	NC 79,684

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SK	R	KUB et al, "Method of Making Mosaic Array of Thin Semiconductor Material of Large Substrates, NC 79,225, Filed 1-16-02, Patent Pending, Serial No. 10/046,534	
SK	S	KUB et al, "Method for Making Shallow Diffusion Junctions in Semiconductors using Elemental Doping, NC 79,596, Filed 9-28-01, Patent Pending, Serial No. 09/964,545	
SK	T	KUB et al, "Method of Manufacturing a Semiconductor Device Having a Thin GaN Material Directly Bonded to an Optimized Substrate", Filed 9-28-01, Patent Pending, Serial No: 09/964,546	
SK	U	KUB et al, "Method for making Electro-Optical Devices Using a Hydrogen Ion Spitting Technique", NC 79,639, Filed 10-29-01, Patent Pending, Serial No. 09/985,958	
SK	V	KUB et al, "Method for Making Piezoelectric Resonator and Surface Acoustic Wave Device Using Hydrogen Implant Layer Splitting, NC 79,598, Filed 4-22-02, Patent Pending, Serial No: Not yet assigned.	
SK	W	KUB et al, "Method for Making Piezoelectric, Electro-Optical and Decoupling Capacitors Using Thin Film Transfer and Hydrogen Ion Splitting Techniques", NC 79,719, Filed 3-18-02, Patent Pending, Serial No. Not Yet Assigned	
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SK	Y	HOBART et al, "Fabrication of SOI Substrates with Ultra-Thin Si Layers, Electronics Letters, 11th June 1998 Vol 34 No. 12	
SK	Z	HOBART et al, "Transfer of BaSb Thin Film to Insulating Substrate via Separation by Hydrogen Implantation", Electronics Letters, 15th April 1999, Vol. 35 No. 8	
SK	AA	HOBART et al, "Single Crystal Ferroelectric Microwave Saplacitor Fabricated by Separation by Hydrogen Implantation", Electronics Letters, 18th March 1999 Vol. 35 No. 6	
SK	BB	M. BRUEL, "Silicon on Insulator Material Technology", Electronics Letters 6th July 1995 Vol. 31 No. 14	

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